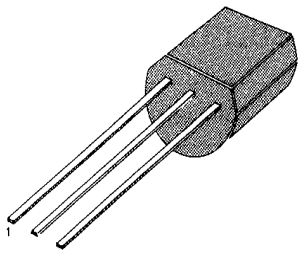
KSP55/56 PNP EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

- Collector-Emitter Voltage: V_{CEO}=KSP55: 60V
  KSP56: 80V
- Collector Dissipation: P_C (max) =625mW

TO-92



1. Emitter 2. Base 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_A=25℃)

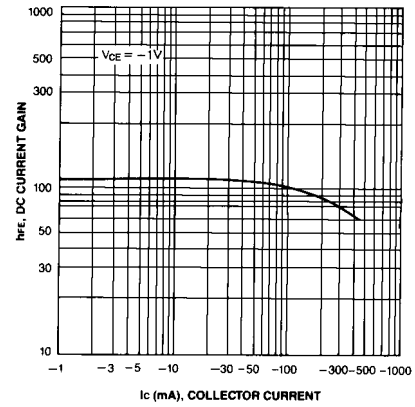
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}		
:KSP55		-60	V
:KSP56		-80	V
Emitter-Base Voltage			
:KSP55	V_{CEO}	-60	V
:KSP56		-80	V
Emitter-Base Voltage	V_{CEO}	-4	V
Collector Current	I_C	-500	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃)

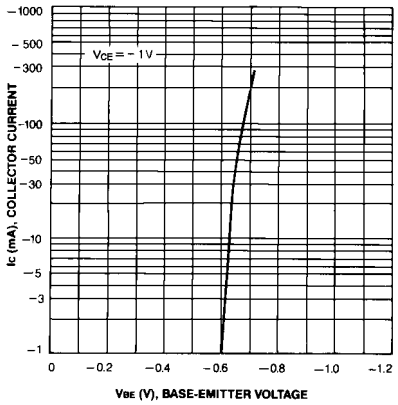
Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -1mA, I_B=0			
:KSP55			-60		V
:KSP56			-80		
Collector-Base Breakdown Voltage	BV_{EBO}	I_E= -100㎂, I_C=0	-4		V
Collector Cut-off Current	I_{CBO}				
:KSP55		V_{CB}= -60V, I_E=0		-0.1	㎂
:KSP56		V_{CB}= -80V, I_E=0		-0.1	㎂
Collector Cut-off Current	I_{CEO}	V_{CE}= -60V, I_B=0		-0.1	㎂
DC Current Gain	h_{FE}	V_{CE}= -1V, I_C= -10mA	50		
		V_{CE}= -1V, I_C= -100mA	50		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C= -100mA, I_B= -10mA		-0.25	V
Base-Emitter On Voltage	V_{BE} (sat)	V_{CE}= -1V, I_C= -100mA		-1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}= -2V, I_C= -10mA f=100MHz	50		MHz

★ Pulse Test: PW ≤ 300㎲, Duty Cycle ≤ 2%

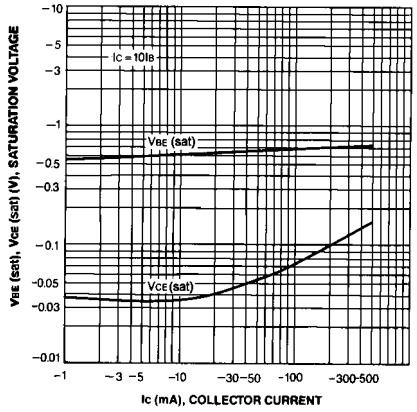
DC CURRENT GAIN



BASE-EMITTER ON VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT